

2SA1188

Silicon PNP Epitaxial

REJ03G0639-0300
(Previous ADE-208-1011A)
Rev.3.00
Aug.10.2005

Application

Low frequency amplifier

Outline

RENESAS Package code: PRSS0003DA-A
(Package name: TO-92 (1))



- 1. Emitter
- 2. Collector
- 3. Base

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-90	V
Collector to emitter voltage	V_{CEO}	-90	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Emitter current	I_E	100	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-90	—	—	V	$I_C = -10\ \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	—	—	V	$I_C = -1\ mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10\ \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.1	μA	$V_{CB} = -70\ V, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.1	μA	$V_{EB} = -2\ V, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800		$V_{CE} = -12\ V,$ $I_C = -2\ mA^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	-0.05	-0.15	V	$I_C = -10\ mA,$ $I_B = -1\ mA^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	-0.7	-1.0	V	
Gain bandwidth product	f_T	—	130	—	MHz	$V_{CE} = -6\ V,$ $I_C = -10\ mA$
Collector output capacitance	C_{ob}	—	3.2	—	pF	$V_{CB} = -10\ V, I_E = 0,$ $f = 1\ MHz$

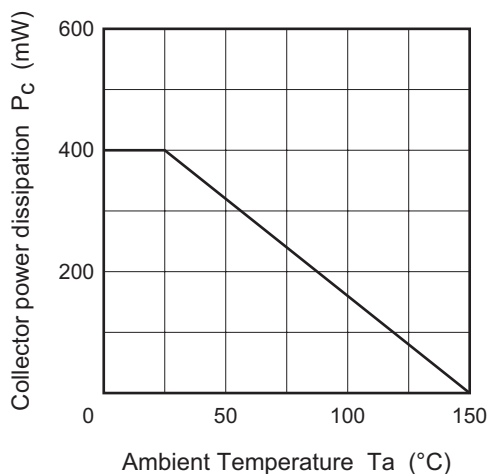
Notes: 1. The 2SA1188 is grouped by h_{FE} as follows.

2. Pulse test

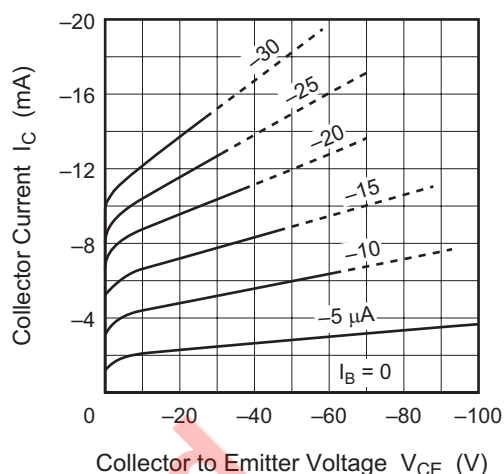
D	E
250 to 500	400 to 800

Main Characteristics

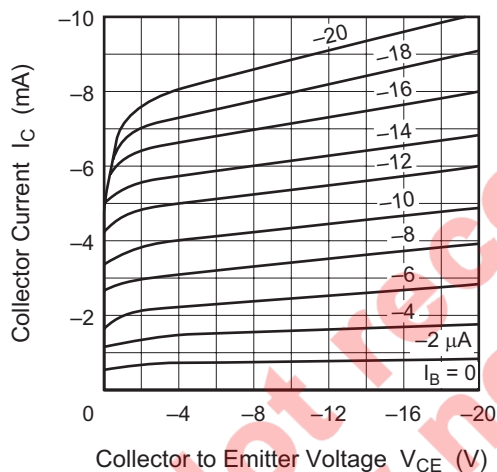
Maximum Collector Dissipation Curve



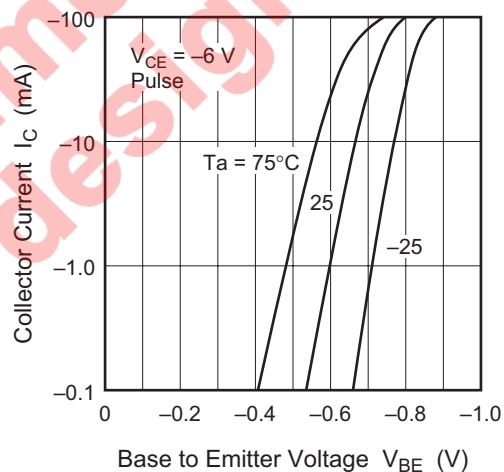
Typical Output Characteristics (1)



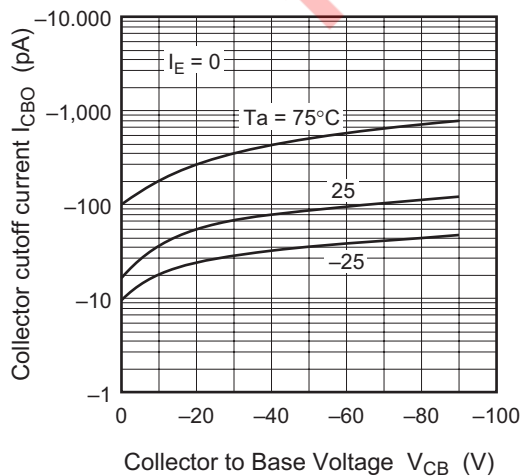
Typical Output Characteristics (2)



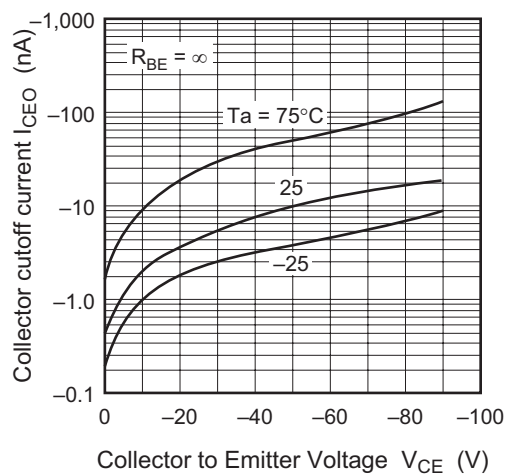
Typical Transfer Characteristics



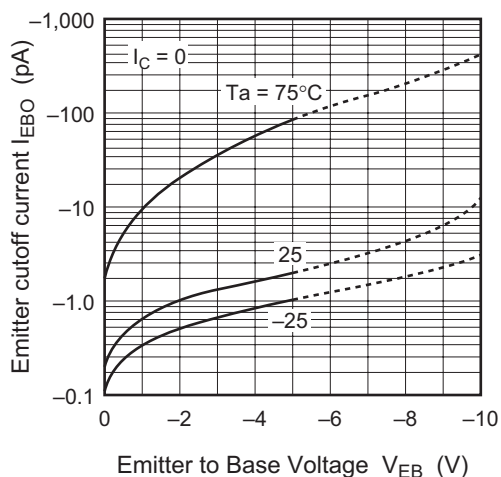
Collector Cutoff Current vs. Collector to Base Voltage



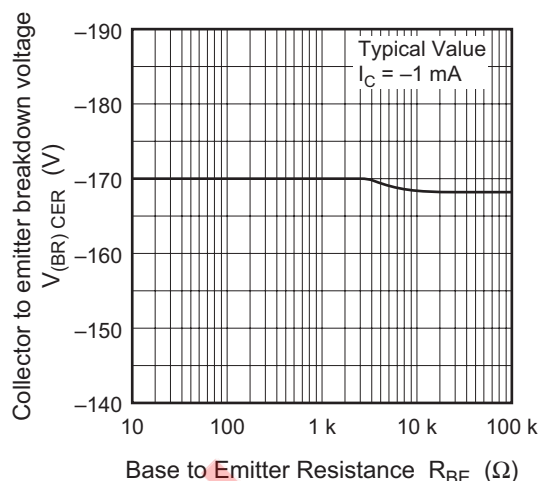
Collector Cutoff Current vs. Collector to Emitter Voltage



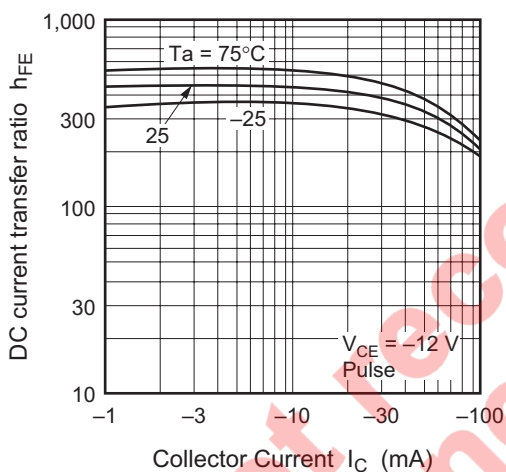
Emitter Cutoff Current vs.
Emitter to Base Voltage



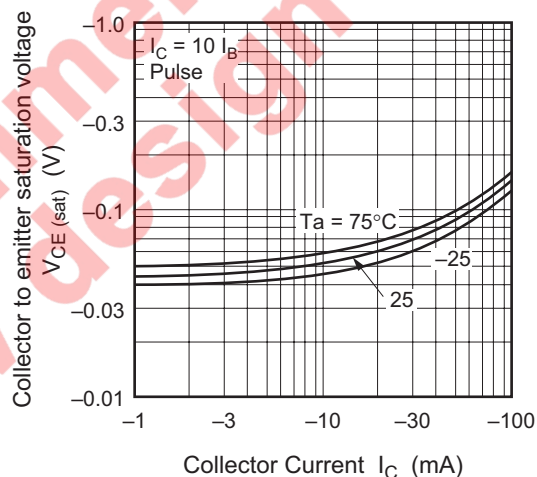
Collector to Emitter Breakdown Voltage vs.
Base to Emitter Resistance



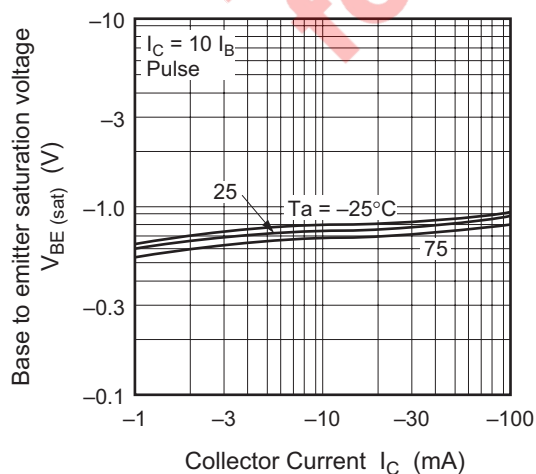
DC Current Transfer Ratio vs.
Collector Current



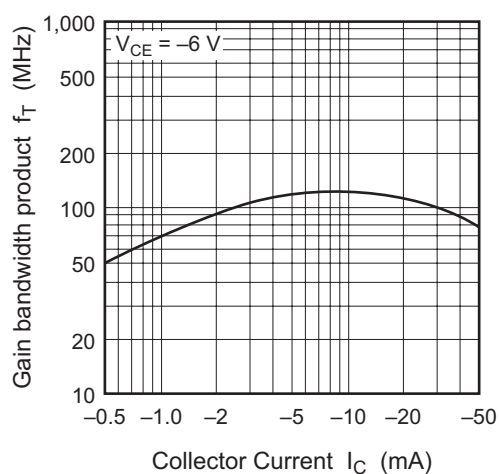
Collector to Emitter Saturation Voltage vs.
Collector Current

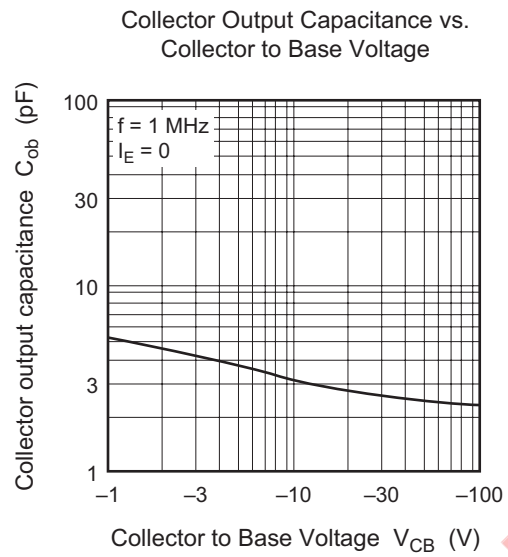


Base to Emitter Saturation Voltage vs.
Collector Current



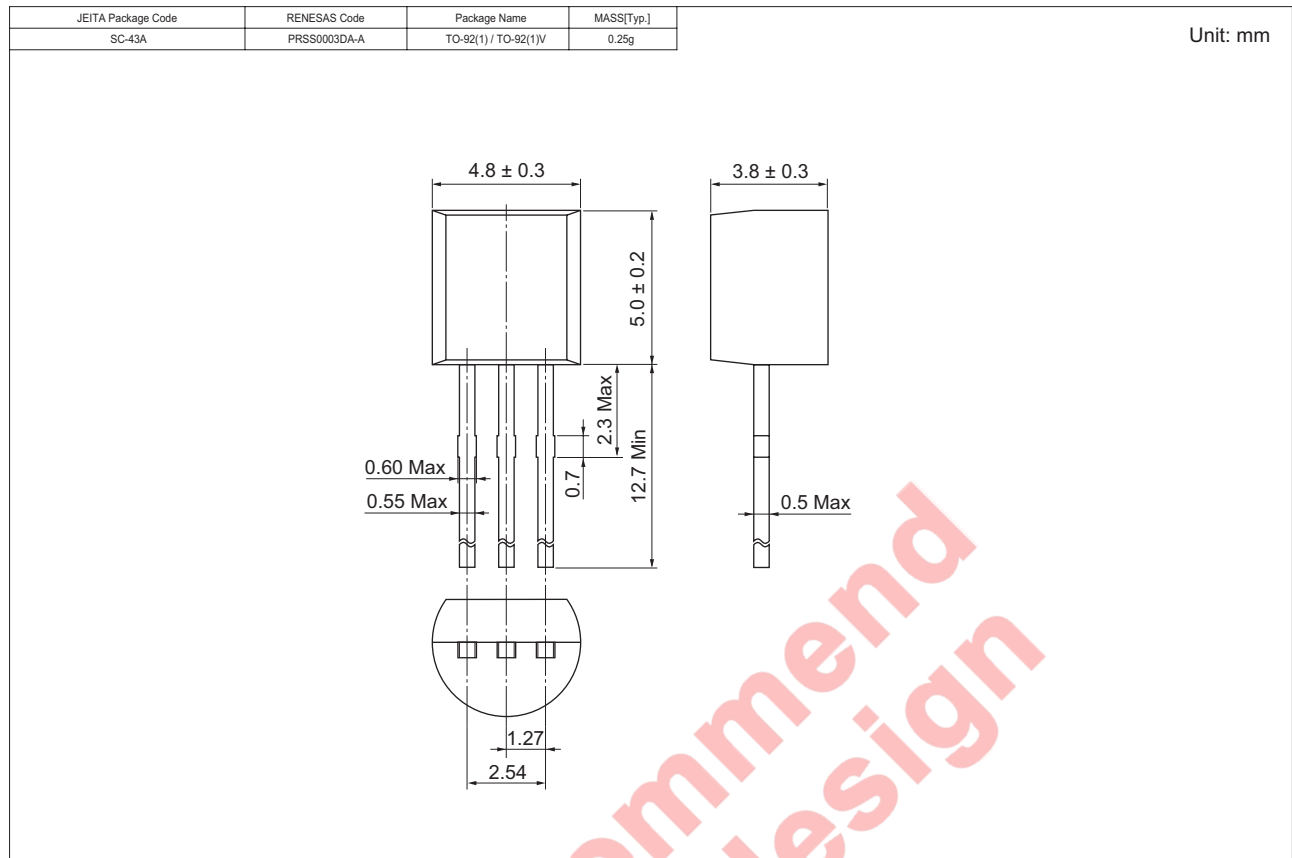
Gain Bandwidth Product vs.
Collector Current





Not recommended
for new design

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SA1188DTZ-E 2SA1188ETZ-E	2500	Hold Box, Radial Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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